## HMC516LC5\* PRODUCT PAGE QUICK LINKS

Last Content Update: 10/05/2017

## COMPARABLE PARTS 🖵

View a parametric search of comparable parts.

## **EVALUATION KITS**

· HMC516LC5 Evaluation Board

## **DOCUMENTATION**

#### **Application Notes**

- AN-1363: Meeting Biasing Requirements of Externally Biased RF/Microwave Amplifiers with Active Bias Controllers
- Broadband Biasing of Amplifiers General Application Note
- MMIC Amplifier Biasing Procedure Application Note
- Thermal Management for Surface Mount Components General Application Note

#### **Data Sheet**

 HMC516LC5: SMT PHEMT Low Noise Amplifier, 9 - 18 GHz Data Sheet

## TOOLS AND SIMULATIONS $\Box$

HMC516LC5 S-Parameters

## REFERENCE MATERIALS 🖵

#### **Quality Documentation**

- Package/Assembly Qualification Test Report: LC5, LC5A (QTR: 2014-00384 REV: 01)
- Semiconductor Qualification Test Report: PHEMT-A (QTR: 2013-00267)

## DESIGN RESOURCES 🖵

- · HMC516LC5 Material Declaration
- PCN-PDN Information
- · Quality And Reliability
- · Symbols and Footprints

## **DISCUSSIONS**

View all HMC516LC5 EngineerZone Discussions.

## SAMPLE AND BUY 🖳

Visit the product page to see pricing options.

## TECHNICAL SUPPORT 🖳

Submit a technical question or find your regional support number.

## DOCUMENT FEEDBACK 🖳

Submit feedback for this data sheet.

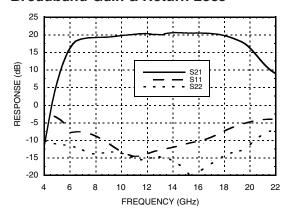
This page is dynamically generated by Analog Devices, Inc., and inserted into this data sheet. A dynamic change to the content on this page will not trigger a change to either the revision number or the content of the product data sheet. This dynamic page may be frequently modified.



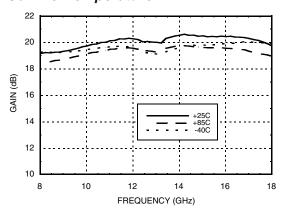
v05.0717

## SMT PHEMT LOW NOISE AMPLIFIER, 9 - 18 GHz

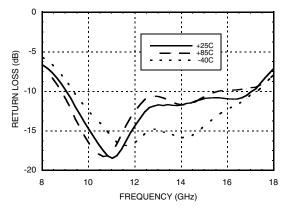
#### **Broadband Gain & Return Loss**



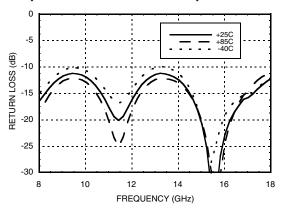
### Gain vs. Temperature



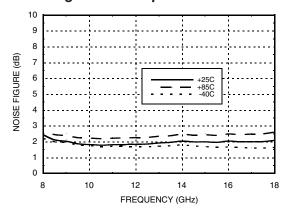
## Input Return Loss vs. Temperature



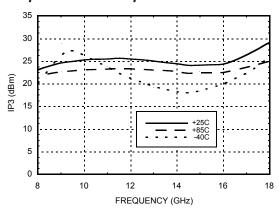
### **Output Return Loss vs. Temperature**



### Noise Figure vs. Temperature



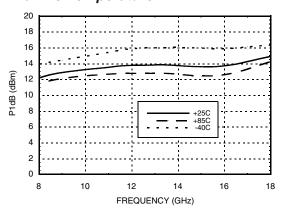
## Output IP3 vs. Temperature



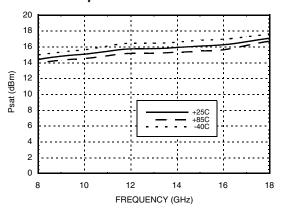


## SMT PHEMT LOW NOISE AMPLIFIER, 9 - 18 GHz

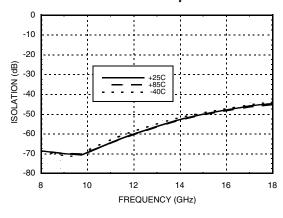
### P1dB vs. Temperature



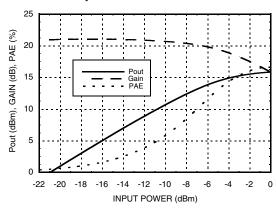
### Psat vs. Temperature



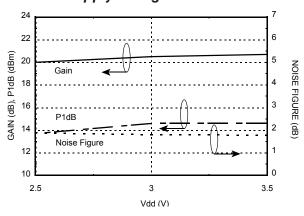
### Reverse Isolation vs. Temperature



### **Power Compression @ 12 GHz**



## Gain, Noise Figure & Power vs. Supply Voltage @ 12 GHz



3



v05.0717

## SMT PHEMT LOW NOISE AMPLIFIER, 9 - 18 GHz

### **Absolute Maximum Ratings**

Drain Bias Voltage (Vdd1, Vdd2, Vdd3)	+4 Vdc	
RF Input Power (RFIN)(Vdd = +3.0 Vdc)	+5 dBm	
Channel Temperature	175 °C	
Continuous Pdiss (T= 85 °C) (derate 14 mW/°C above 85 °C)	1.17 W	
Thermal Resistance (channel to die bottom)	76.9 °C/W	
Storage Temperature	-65 to +150 °C	
Operating Temperature	-40 to +85 °C	
ESD Sensitivity (HBM)	Class 1A	

## Typical Supply Current vs. Vdd

Vdd (V)	Idd (mA)
+2.5	61
+3.0	65
+3.5	69

Note: Amplifier will operate over full voltage range shown above.



ELECTROSTATIC SENSITIVE DEVICE OBSERVE HANDLING PRECAUTIONS

## **Outline Drawing**

#### **BOTTOM VIEW** 0.197±.005 PIN 32 .014 \[ 0.36 \] .009 \[ 0.24 \] 013 [0.32] [5.00±.13] 32 25 PIN 1 $\Box$ 1 24 D H516 0.197±.005 [5.00±.13] $\Box$ $\Box$ XXXX D 0.56 $\Box$ $\Box$ 8 17 $\Box$ 16 .138 [3.50] **EXPOSED** LOT NUMBER SQUARE GROUND 0.044 [1.12] .161 [4.10] PADDLE MAX **SEATING** NOTES: PLANE 1. PACKAGE BODY MATERIAL: ALUMINA -C-

- 2. LEAD AND GROUND PADDLE PLATING: 30-80 MICROINCHES GOLD OVER 50 MICROINCHES MINIMUM NICKEL
- 3. DIMENSIONS ARE IN INCHES [MILLIMETERS]
- 4. LEAD SPACING TOLERANCE IS NON-CUMULATIVE
- 5. PACKAGE WARP SHALL NOT EXCEED 0.05mm DATUM
- 6. ALL GROUND LEADS AND GROUND PADDLE MUST BE SOLDERED TO PCB RF GROUND

### Package Information

Part Number	Package Body Material	Lead Finish	MSL Rating	Package Marking [2]
HMC516LC5	Alumina, White	Gold over Nickel	MSL3 <sup>[1]</sup>	H516 XXXX

<sup>[1]</sup> Max peak reflow temperature of 260 °C

<sup>[2] 4-</sup>Digit lot number XXXX



# SMT PHEMT LOW NOISE AMPLIFIER, 9 - 18 GHz

## **Pin Descriptions**

Pin Number	Function	Description	Interface Schematic	
1, 2, 6 - 19, 23 - 24, 32	GND	This pin may be connected to RF/DC ground. Performance will not be affected.		
4	RFIN	This pin is AC coupled and matched to 50 Ohms.	RFIN ○──  ├──	
30, 28, 26	Vdd1, 2, 3	Power Supply Voltage for the amplifier. External bypass capacitors of 100 pF and 2.2 μF are required.	OVdd1,2,3	
21	RFOUT	This pin is AC coupled and matched to 50 Ohms.	—   —○ RFOUT	
3, 5, 20, 22, 25, 27, 29, 31 GND These pins and package bottom must be connected to RF/DC ground.		= O GND		

## **Application Circuit**

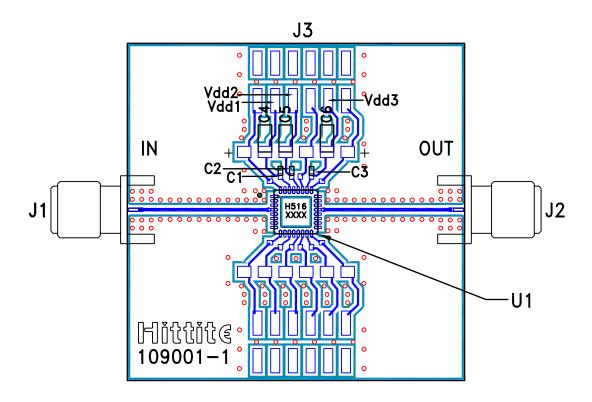
Component	Value	Vdd1	Vdd2	Vdd3	
C1, C2, C3	100 pF	φ	φ	φ	
C4, C5, C6	2.2 μF				
		±C1 C4±	±C2 C5±	<u></u> C3   C6 <u></u>	
		<u>+   +</u>	+   +	<u> </u>	
		_   _	_   _	_   _	
		30	20	26	
		30	28	20	
	RFIN	4		21	— ✓ RFOUT
	KI IIV	'		21	(11 001



v05.0717

## SMT PHEMT LOW NOISE AMPLIFIER, 9 - 18 GHz

#### **Evaluation PCB**



#### List of Materials for Evaluation PCB 110431 [1]

Item	Description	
J1 - J2	PCB Mount K Connector	
J3	2 mm DC Header	
C1 - C3	100 pF Capacitor, 0402 Pkg.	
C4 - C6	2.2 µF Capacitor, Tantalum	
U1	HMC516LC5 Amplifier	
PCB [2]	PCB [2] 109001 Evaluation PCB	

<sup>[1]</sup> Reference this number when ordering complete evaluation PCB  $\,$ 

The circuit board used in the application should use RF circuit design techniques. Signal lines should have 50 Ohm impedance while the package ground leads and exposed paddle should be connected directly to the ground plane similar to that shown. A sufficient number of via holes should be used to connect the top and bottom ground planes. The evaluation board should be mounted to an appropriate heat sink. The evaluation circuit board shown is available from Analog Devices, upon request.

<sup>[2]</sup> Circuit Board Material: Rogers 4350